

**Listing of Claims**

The following listing of claims replaces all prior versions and listings of claims in the application.

1. (Original): A polishing slurry comprising:  
a metal-oxidizing agent; a metal anticorrosive agent; an oxidized metal dissolving agent;  
and water,

wherein the oxidized metal dissolving agent is at least one kind selected from the group consisting of an acid in which the dissociation constant (pKa) of a first dissociable acid group is 3.5 or more, an ammonium salt of the acid and an organic acid ester of the acid, the pH of the polishing slurry is within the range of 3 to 4, and the concentration of the metal-oxidizing agent is within the range of 0.01 to 3 percent by weight.

2. (Original): The polishing slurry of claim 1, wherein the concentration of the oxidizing agent is within the range of 0.01 to 1.5 percent by weight.

3. (Currently amended): The polishing slurry of claim 1 [[or 2]], wherein the oxidized metal dissolving agent is an organic acid.

4. (Original): The polishing slurry of claim 3, wherein the organic acid is at least one kind selected from the group consisting of lactic acid, succinic acid, adipic acid, glutaric acid, benzoic acid, quinaldic acid, butyric acid and valeric acid.

5. (Currently amended): The polishing slurry of ~~any one of claims 1 to 4~~ claim 1, wherein the metal anticorrosive agent is at least one kind selected from the group consisting of a compound having a triazole skeleton other than benzotriazole, a compound having a pyrimidine skeleton, a compound having an imidazole skeleton, a compound having a guanidine skeleton, a compound having a thiazole skeleton, a compound having a pyrazole skeleton and benzotriazole.

6. (Currently amended): The polishing slurry of ~~any one of claims 1 to 5~~ claim 1, wherein the metal-oxidizing agent is at least one kind selected from the group consisting of hydrogen peroxide, ammonium persulfate, ferric nitrate, nitric acid, potassium periodate, hypochlorous acid and ozone water.

7. (Currently amended): The polishing slurry of ~~any one of claims 1 to 6~~ claim 1, wherein the polishing slurry contains polishing particles.

8. (Original): The polishing slurry of claim 7, wherein the polishing particles are at least one kind selected from the group consisting of silica, alumina, ceria, titania, zirconia and germania.

9. (Currently amended): The polishing slurry of claim 7 [[or 8]], wherein the polishing particles are colloidal silica or colloidal alumina having an average particle diameter of 100 nm or less.

10. (Currently amended): The polishing slurry of ~~any one of claims 1 to 9~~ claim 1, wherein the polishing slurry contains a water-soluble polymer compound.

11. (Original): The polishing slurry of claim 10, wherein the water-soluble polymer compound is at least one kind selected from the group consisting of polyacrylic acid and the salt thereof, polymethacrylic acid and the salt thereof, polyacrylamide, polyvinyl alcohol, and polyvinylpyrrolidone.

12. (Currently amended): A polishing method comprising:  
a first polishing step of polishing a conductive substance layer of a substrate having an interlaminar insulating film of which the surface consists of dented portions and projected portions, a barrier conductor layer coating the interlaminar insulating film along the surface thereof, and the conductive substance layer with which the dented portions are filled up and coats the barrier conductor layer to expose the barrier conductor layer of the projected portions; and  
a second polishing step of polishing chemically and mechanically polishing at least the barrier conductor layer and the conductive substance layer of the dented portions while supplying the polishing slurry of ~~any one of claims 1 to 11~~ claim 1 to expose the interlaminar insulating film of the projected portions.

13. (Original): The polishing method of claim 12, wherein the barrier conductor layer prevents the conductive substance from diffusing to the interlaminar insulating film, and the conductive substance is at least one of copper and a copper alloy.

14. (Currently amended): The polishing method of claim 12 [[or 13]], wherein the barrier conductor layer is a single layer made of one kind or a lamination layer made of two kinds or more selected from the group consisting of tantalum, tantalum nitride, a tantalum alloy, titanium, titanium nitride, a titanium alloy, tungsten, tungsten nitride and a tungsten alloy.